

Vol. 15: January 2004

Color Code:

Red – Plasma Etching

Blue – Advanced Devices

For full patent test, please use patent number search feature at United States Patent and Trademark Office:

<http://patft.uspto.gov/netahtml/srchnum.htm>

US Patent Nr.	Title	Assignee	Filed	Date of Patent
6,660,646	Method for plasma hardening photoresist in etching of semiconductor and superconductor films	Northrop Grumman Corporation	9/21/00	12/9/03
6,664,195	Method for forming damascene metal gate	Hynix Semiconductor, Inc.	10/12/01	12/16/03
6,664,582	Fin memory cell and method of fabrication	International Business Machines Corporation	4/12/02	12/16/03
6,664,598	Polysilicon back-gated SOI MOSFET for dynamic threshold voltage control	International Business Machines Corporation	9/5/02	12/16/03
6,667,227	Trenched gate metal oxide semiconductor device and method	Advanced Micro Devices, Inc.	3/17/00	12/23/03
6,667,512	Asymmetric retrograde halo metal-oxide-semiconductor field-effect transistor (MOSFET)	Advanced Micro Devices, Inc.	3/31/00	12/23/03
6,670,278	Method of plasma etching of silicon carbide	Lam Research Corporation	3/30/01	12/30/03

6,670,642	Semiconductor memory device using vertical-channel transistors	Renesas Technology Corporation	1/22/02	12/30/03
6,673,199	Shaping a plasma with a magnetic field to control etch rate uniformity	Applied Materials, Inc.	3/7/01	1/6/04
6,673,683	Damascene gate electrode method for fabricating field effect transistor (FET) device with ion implanted lightly doped extension regions	Taiwan Semiconductor Manufacturing Co.	11/7/02	1/6/04
6,674,100	SiGeC-based CMOSFET with separate heterojunctions	Matsushita Electric Industrial Co.	4/5/02	1/6/04
6,674,139	Inverse T-gate structure using damascene processing	International Business Machines Corporation	7/20/01	1/6/04
6,677,246	Endpoint detection in the etching of dielectric layers	Scientific Systems Research Ltd.	12/6/01	1/13/04
6,677,624	Carbon nanotubes transistor	Hyundai Electronics Industries Co.	9/17/02	1/13/01